

Supporting Information

Improving the performance of quantum dot sensitized solar cells through CdNiS quantum dots with reduced recombination and enhanced electron life time

**Chandu V.V.M. Gopi,^a Mallineni Venkata-Haritha,^a Hyunwoong Seo,^b Saurabh Singh,^c
Soo-Kyoung Kim,^d Masaharu Shiratani,^b and Hee-Je Kim^{a*}**

^a *School of Electrical Engineering, Pusan National University, Busandaehak-ro 63beon-gil,
Geumjeong-gu, Busan, 46241, South Korea*

^b *Department of Electronics, Kyushu university, 744 Motooka, Nishi-ku, Fukuoka, 819-0395,
Japan*

^c *School of Materials Science & Engineering, Pusan National University, Busan 46241, South
Korea*

^d *Kyeongnam Technopark 22, Changwon-daero 18beon-gil, Uichang-gu, Changwon-si,
Gyeongsangnam-do, 51395, South Korea*

*Corresponding authors. Tel.: +82 51 510 2364; fax: +82 51 513 0212

E-mail: heeje@pusan.ac.kr (H.-J. Kim)

Table S1. Composition of elements in CdS, 5%CdNiS, 10%CdNiS, 15%CdNiS, and 20%CdNiS electrodes using energy dispersive X-ray spectroscopy (EDS) analysis.

Electrodes	Atomic (%)				
	Ti	O	Cd	Ni	S
CdS	25.99	53.67	8.88	-	11.46
5%CdNiS	25.82	53.62	8.38	0.76	11.42
10%CdNiS	26.03	53.45	8.13	0.94	11.45
15%CdNiS	26.09	53.37	7.89	1.19	11.46
20%CdNiS	26.08	53.34	7.56	1.53	11.49

Table S2. Solar cell parameters of QDSSC (multiple cells) with CdS and Ni-doped CdS photoanodes.

Counter Electrode	V_{oc} (V)	J_{SC} (mA cm⁻²)	FF	η (%)
CdS (Cell 1)	0.601	7.39	0.451	2.00
CdS (Cell 2)	0.603	7.40	0.451	2.01
CdS (Cell 3)	0.604	7.37	0.452	2.02
5% CdNiS (Cell 1)	0.619	7.54	0.504	2.36
5% CdNiS (Cell 2)	0.612	7.60	0.506	2.36
5% CdNiS (Cell 3)	0.617	7.55	0.502	2.34
10% CdNiS (Cell 1)	0.619	8.01	0.493	2.45
10% CdNiS (Cell 2)	0.626	7.99	0.485	2.42
10% CdNiS (Cell 3)	0.637	8.01	0.495	2.47
15% CdNiS (Cell 1)	0.643	8.91	0.543	3.11
15% CdNiS (Cell 2)	0.633	9.02	0.553	3.16
15% CdNiS (Cell 3)	0.639	8.95	0.542	3.10
20% CdNiS (Cell 1)	0.623	8.78	0.541	2.96
20% CdNiS (Cell 2)	0.629	8.73	0.545	2.99
20% CdNiS (Cell 3)	0.611	8.86	0.541	2.93

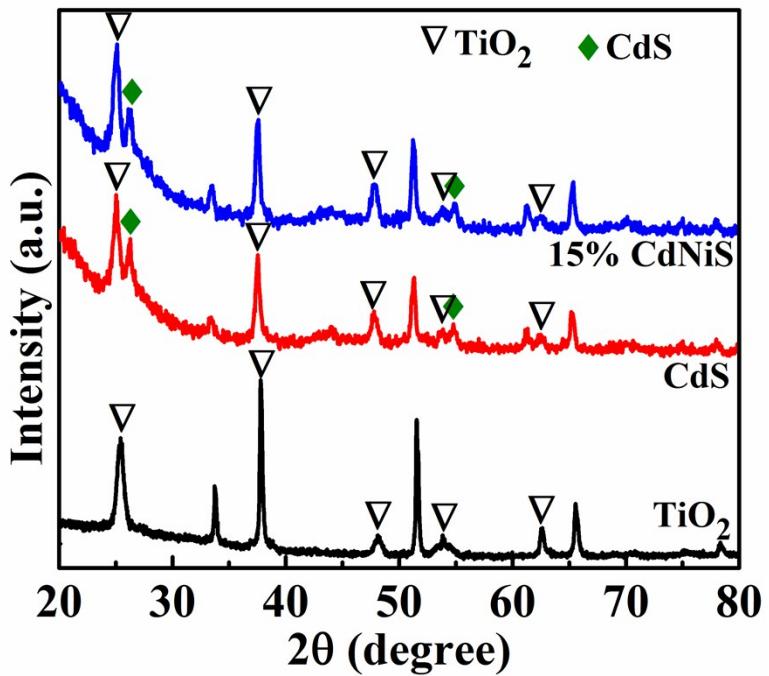


Fig. S1 XRD patterns of the TiO_2 , CdS and 15% CdNiS films.